

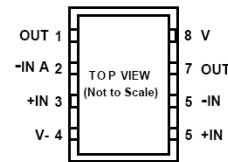
FEATURES

- Rail-to-Rail Input/Output**
- Low Power: 650 μ A typ**
- Wide bandwidth: 8.3 MHz Unity Gain Bandwidth**
- Low offset voltage: 100 μ V max @ 25°C**
- Unity-gain stable**
- High slew rate: 4.0 V/ μ s typ**
- Low noise: 3.9 nV/ \sqrt Hz typ**

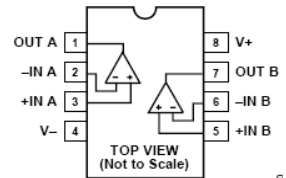
APPLICATIONS

- Battery-powered instrumentation**
- Power supply control and protection**
- Telecom**
- DAC output amplifier**
- ADC input buffer**

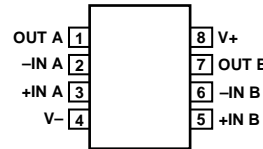
PIN CONFIGURATIONS



8-Lead LFCSP (CP)



8-Lead MSOP (RM-8)



8-Lead LFCSP (CP)

GENERAL DESCRIPTION

ADA4084-2 is a dual amplifier featuring 650 μ A per amplifier with single-supply operation, 8.3 MHz bandwidth, and rail-to-rail inputs and outputs. They are guaranteed to operate from 3 V to 30 V single supplies or ± 1.5 V to ± 15 V dual supplies.

These amplifiers are superb for single-supply and dual applications requiring both AC and precision DC performance with input voltage range and output swings very close to the power supply rails. The combination of bandwidth, low noise, low power, and precision makes the ADA4084 useful in a wide variety of applications, including filters and instrumentation.

Other applications for these amplifiers include portable telecom equipment, power supply control and protection, and as amplifiers or buffers for transducers with wide output ranges. Sensors requiring a rail-to-rail input amplifier include Hall Effect, piezoelectric, and resistive transducers.

The ability to swing rail-to-rail at both the input and output enables designers to build multistage filters in single-supply systems and to maintain high signal-to-noise ratios.

The ADA4084-2 is specified over the extended industrial temperature range of -40°C to $+125^{\circ}\text{C}$. The ADA4084-2 is a dual available in 8-lead LFCSP (3x3mm), SOIC, and MSOP packages.

Table 1. 30V Rail-to-Rail I/O Op Amps

	Precision	Precision Low Power	Low Power
Single	OP184		
Dual	OP284	ADA4091-2	ADA4092-2
Quad	OP484	ADA4091-4	ADA4092-4

Rev. PrA

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A.

Tel: 781.329.4700

Fax: 781.461.3113

www.analog.com

© 2011 Analog Devices, Inc. All rights reserved.

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS – VS = ±15V

VS = ±15 V @ TA = 25°C, VCM = 0 V, VOUT = 0 V, unless otherwise noted.

Table 2.

Parameter	Symbol	Test Conditions / Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Voltage Offset	VOs	-40 °C ≤ TA ≤ +125°C			100	μV
Offset Voltage Drift	ΔVOs/ΔT	-40 °C ≤ TA ≤ +125°C		0.2	300	μV/°C
Input Bias Current	IB	-40 °C ≤ TA ≤ +125°C		80	450	nA
Bias Current Drift	ΔIB/ΔT	-40 °C ≤ TA ≤ +125°C			575	nA
Input Offset Current	Ios	-40 °C ≤ TA ≤ +125°C		150		pA/°C
Input Voltage Range			-15		TBD	V
Common-Mode Rejection Ratio	CMRR	VCM = ±14 V, -40 °C ≤ TA ≤ +125°C	86	90		dB
		VCM = ±15 V	80			dB
Large Signal Voltage Gain	AVO	RL = 2 kΩ, -13.5 V ≤ VO ≤ +13.5 V	104	120		dB
		-40°C ≤ TA ≤ +125°C	97			dB
Input Resistance, Differential Mode	RINDM			TBD		Ω
Input Resistance, Common Mode	RINCM			TBD		Ω
Input Capacitance, Differential Mode	CINDM			TBD		pF
Input Capacitance, Common Mode	CINCM			TBD		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	VOH	RL = 10 kΩ to GND	14.8	TBD		V
		-40 °C ≤ TA ≤ +125°C	TBD			V
		RL = 2 kΩ to GND	14.7	TBD		V
		-40 °C ≤ TA ≤ +125°C	TBD			V
Output Voltage Low	VOL	RL = 10 kΩ to GND		TBD	-14.8	V
		-40 °C ≤ TA ≤ +125°C			TBD	V
		RL = 2 kΩ to GND		TBD	-14.7	V
		-40 °C ≤ TA ≤ +125°C			TBD	V
Output Current	ISC			±10		mA
Output Closed-Loop Impedance	ZOUT			TBD		Ω
POWER SUPPLY						
Power Supply Rejection	PSRR	VS = ±2V to ±18 V	90	TBD		dB
		-40 °C ≤ TA ≤ +125°C	TBD			dB
Quiescent Current	ISY	IO = 0mA		650	750	μA
		-40°C ≤ TA ≤ +125°C			1000	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	RL = 2 kΩ	2.4	4		V/μs
Unity Gain Bandwidth	UGB			8.3		MHz
Gain Bandwidth Product	GBWP			TBD		MHz
-3dB Bandwidth	-3dB			TBD		MHz
Full Power Bandwidth	BWP	1% distortion, RL = 2 kΩ, VO = 29 V p-p		TBD		kHz
Settling Time	ts	To 0.01%, 10 V step		TBD		μs
Total Harmonic Distortion + Noise	THD+N			TBD		%
Phase Margin	∅M			60		Degrees
NOISE PERFORMANCE						
Input Voltage Noise	enp-p	0.1 Hz to 10 Hz		0.1		μV p-p
Input Voltage Noise Density	en	f = 1 kHz		3.9		nV/√Hz
Input Current Noise Density	in	f = 1 kHz		TBD		pA/√Hz

ELECTRICAL CHARACTERISTICS – VS = ±5V

VS = ±5 V @ TA = 25°C, VCM = 0 V, VOUT = 0 V, unless otherwise noted.

Table 3.

Parameter	Symbol	Test Conditions / Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Voltage Offset	V _{OS}				100 300	μV μV
Offset Voltage Drift	ΔV _{OS} /ΔT	-40 °C ≤ T _A ≤ +125°C		0.2		μV/°C
Input Bias Current	I _B	-40 °C ≤ T _A ≤ +125°C		80	450	nA
Bias Current Drift	ΔI _B /ΔT	-40 °C ≤ T _A ≤ +125°C			575	nA
Input Offset Current	I _{OS}			150		pA/°C
Input Voltage Range		-40 °C ≤ T _A ≤ +125°C			50	nA
Common-Mode Rejection Ratio	CMRR	V _{CM} = ±4 V, -40 °C ≤ T _A ≤ +125°C	-5		TBD	V
		V _{CM} = ±5 V	86	90	+5	dB
Large Signal Voltage Gain	A _{VO}	R _L = 2 kΩ, -4 V ≤ V _O ≤ +4 V	80			dB
		-40°C ≤ T _A ≤ +125°C	104	120		dB
Input Resistance, Differential Mode	R _{INDM}			TBD		Ω
Input Resistance, Common Mode	R _{INCM}			TBD		Ω
Input Capacitance, Differential Mode	C _{INDM}			TBD		pF
Input Capacitance, Common Mode	C _{INCM}			TBD		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	V _{OH}	R _L = 10 kΩ to GND	4.8	TBD		V
		-40 °C ≤ T _A ≤ +125°C	TBD			V
		R _L = 2 kΩ to GND	4.7	TBD		V
		-40 °C ≤ T _A ≤ +125°C	TBD			V
Output Voltage Low	V _{OL}	R _L = 10 kΩ to GND		TBD	-4.8	V
		-40 °C ≤ T _A ≤ +125°C			TBD	V
		R _L = 2 kΩ to GND		TBD	-4.7	V
		-40 °C ≤ T _A ≤ +125°C			TBD	V
Output Current	I _{SC}			±10		mA
Output Closed-Loop Impedance	Z _{OUT}			TBD		Ω
POWER SUPPLY						
Power Supply Rejection	PSRR	V _S = ±2 to ±18 V	90	TBD		dB
		-40 °C ≤ T _A ≤ +125°C	TBD			dB _Ω
Quiescent Current	I _{SY}	I _O = 0mA		650	750	μA
		-40°C ≤ T _A ≤ +125°C			1000	μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	R _L = 2 kΩ	2.4	4		V/μs
Unity Gain Bandwidth	UGB			8.3		MHz
Gain Bandwidth Product	GBWP			TBD		MHz
-3dB Bandwidth	-3dB			TBD		MHz
Full Power Bandwidth	BW _P	1% distortion, R _L = 2 kΩ, V _O = 9 V _{p-p}		TBD		kHz
Settling Time	t _S	To 0.01%		TBD		μs
Total Harmonic Distortion + Noise	THD+N			TBD		%
Phase Margin	∅ _M			60		Degrees
NOISE PERFORMANCE						
Input Voltage Noise	e _{np-p}	0.1 Hz to 10 Hz		0.1		μV p-p
Input Voltage Noise Density	e _n	f = 1 kHz		3.9		nV/√Hz
Input Current Noise Density	i _n	f = 1 kHz		TBD		pA/√Hz

ELECTRICAL CHARACTERISTICS – VS = +3V

VS = +3 V @ TA = 25°C, VCM = +1.5 V, unless otherwise noted.

Table 4.

Parameter	Symbol	Test Conditions / Comments	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Voltage Offset	VOs	-40 °C ≤ TA ≤ +125°C			100 300	μV μV
Offset Voltage Drift	ΔVOs/ΔT	-40 °C ≤ TA ≤ +125°C		0.2		μV/°C
Input Bias Current	IB	-40 °C ≤ TA ≤ +125°C		80	450 575	nA nA
Bias Current Drift	ΔIB/ΔT			150		pA/°C
Input Offset Current	Ios	-40 °C ≤ TA ≤ +125°C			50 TBD	nA nA
Input Voltage Range			0		3	V
Common-Mode Rejection Ratio	CMRR	VCM = 0 V to 3V -40 °C ≤ TA ≤ +125°C	86 80	90		dB dB
Large Signal Voltage Gain	AVO	RL = 2 kΩ, 0.5 ≤ VO ≤ +2.5 V -40°C ≤ TA ≤ +125°C	104 97	120		dB dB
Input Resistance, Differential Mode	RINDM			TBD		Ω
Input Resistance, Common Mode	RINCM			TBD		Ω
Input Capacitance, Differential Mode	CINDM			TBD		pF
Input Capacitance, Common Mode	CINCM			TBD		pF
OUTPUT CHARACTERISTICS						
Output Voltage High	VOH	RL = 10 kΩ to VCM -40 °C ≤ TA ≤ +125°C	2.8 TBD	TBD		V V
		RL = 2 kΩ to VCM -40 °C ≤ TA ≤ +125°C	2.7 TBD	TBD		V V
Output Voltage Low	VOL	RL = 10 kΩ to VCM -40 °C ≤ TA ≤ +125°C		TBD	0.2	V V
		RL = 2 kΩ to VCM -40 °C ≤ TA ≤ +125°C		TBD	0.3	V V
Output Current	ISC			±10		mA
Output Closed-Loop Impedance	ZOUT			TBD		Ω
POWER SUPPLY						
Power Supply Rejection	PSRR	VS = ±1.25 to ±1.75 V -40 °C ≤ TA ≤ +125°C	90 TBD	TBD		dB dB
Quiescent Current	ISY	Io = 0mA -40°C ≤ TA ≤ +125°C		650	750 1000	μA μA
DYNAMIC PERFORMANCE						
Slew Rate	SR	RL = 2 kΩ	2.4	4		V/μs
Unity Gain Bandwidth	UGB	TBD		8.3		MHz
Gain Bandwidth Product	GBWP	TBD		TBD		MHz
-3dB Bandwidth	-3dB	TBD		TBD		MHz
Full Power Bandwidth	BWP	1% distortion, RL = 2 kΩ, VO = TBD		35		kHz
Settling Time	ts	To 0.01%		TBD		μs
Total Harmonic Distortion + Noise	THD+N			TBD		%
Phase Margin	∅M			60		Degrees
NOISE PERFORMANCE						
Input Voltage Noise	enp-p	0.1 Hz to 10 Hz		0.1		μV p-p
Input Voltage Noise Density	en	f = 1 kHz		3.9		nV/√Hz
Input Current Noise Density	in	f = 1 kHz		TBD		pA/√Hz

ABSOLUTE MAXIMUM RATINGS

Table 5.

Parameter	Rating
Supply Voltage	36 V
Input Voltage	$\pm V$ supply
Differential Input Voltage	$V^- \leq (+IN - -IN) \leq V^+$
Output Short-Circuit Duration to Gnd	Indefinite
Storage Temperature Range	-65°C to +150°C
Operating Temperature Range	-40°C to +125°C
Junction Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 60 sec)	300°C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages.

Table 6. Thermal Resistance

Package Type	θ_{JA}	θ_{JC}	Unit
8-Lead SOIC (R-8)	TBD	TBD	°C/W
8-Lead MSOP (RM-8)	TBD	TBD	°C/W
8-Lead LFCSP (CP-8)	TBD	TBD	°C/W

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.